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DS90CF386MTDX/NOPB

Texas instruments

LVDS Interface IC 3.3V LVDS Receiver 24B FPD Link 85MHz

Any questions, please feel free to contact us. info@kaimte.com













DS90CF366, DS90CF386

SNLS055J-NOVEMBER 1999-REVISED MAY 2016

DS90CF3x6 3.3-V LVDS Receiver 24-Bit Or 18-Bit Flat Panel Display (FPD) Link, 85 MHz

1 Features

- 20-MHz to 85-MHz Shift Clock Support
- Rx Power Consumption <142 mW (Typical) at 85-MHz Grayscale
- Rx Power-Down Mode <1.44 mW (Maximum)
- ESD Rating >7 kV (HBM), >700 V (EIAJ)
- Supports VGA, SVGA, XGA, and Single Pixel SXGA
- PLL Requires No External Components
- Compatible With TIA/EIA-644 LVDS Standard
- Low Profile 56-Pin or 48-Pin TSSOP Package
- DS90CF386 Also Available in a 64-Pin, 0.8-mm, Fine Pitch Ball Grid Array (NFBGA) Package

2 Applications

- Video Displays
- · Printers and Imaging
- Digital Video Transport
- Machine Vision
- Open LDI-to-RGB Bridge

3 Description

The DS90CF386 receiver converts four LVDS (Low Voltage Differential Signaling) data streams back into parallel 28 bits of LVCMOS data. Also available is the DS90CF366 receiver that converts three LVDS data streams back into parallel 21 bits of LVCMOS data. The outputs of both receivers strobe on the falling edge. A rising edge or falling edge strobe transmitter will interoperate with a falling edge strobe receiver without any translation logic.

The receiver LVDS clock operates at rates from 20 MHz to 85 MHz. The device phase-locks to the input LVDS clock, samples the serial bit streams at the LVDS data lines, and converts them into parallel output data. At an incoming clock rate of 85 MHz, each LVDS input line is running at a bit rate of 595 Mbps, resulting in a maximum throughput of 2.38 Gbps for the DS90CF386 and 1.785 Gbps for the DS90CF366.

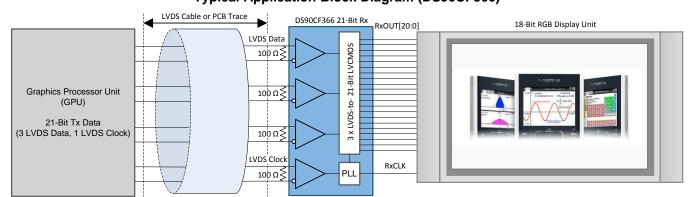
The use of these serial link devices is ideal for solving EMI and cable size problems associated with transmitting data over wide, high-speed parallel LVCMOS interfaces. Both devices are offered in TSSOP packages. The DS90CF386 is also offered in a 64-pin, 0.8-mm, fine pitch ball grid array (NFBGA) package which provides a 44% reduction in PCB footprint compared to the 56-pin TSSOP package.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
DS90CF366	TSSOP (48)	12.50 mm × 6.10 mm
DS90CF386	TSSOP (56)	14.00 mm × 6.10 mm
D390CF300	NFBGA (64)	8.00 mm × 8.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Typical Application Block Diagram (DS90CF366)



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision I (April 2013) to Revision J

Page

•	Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and	
	Mechanical, Packaging, and Orderable Information section	1
•	Changed Figure 8 and Figure 9 to clarify that TxIN on Tx is the same as RxOUT on Rx	12
•	Changed title of DS90CF366 mapping to clarify the make-up of the LVDS lines	13
•	Deleted references to power sequencing requirements for FPD-Link I transmitters	19

Changes from Revision H (April 2013) to Revision I

Page

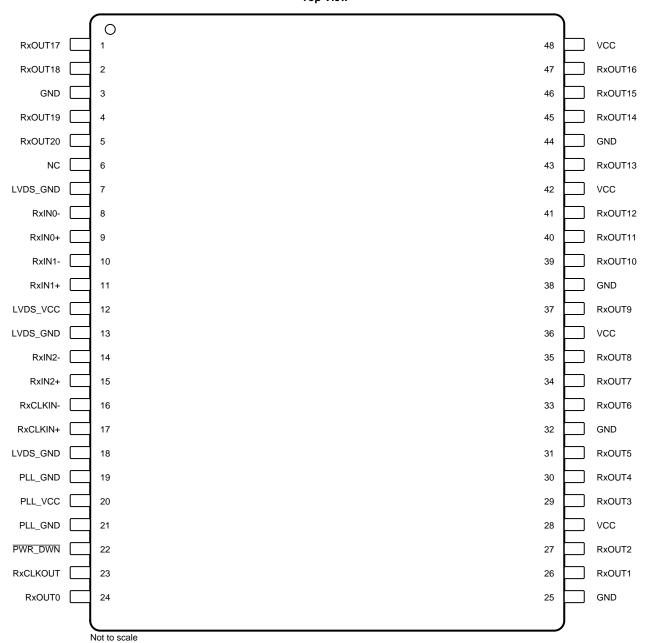
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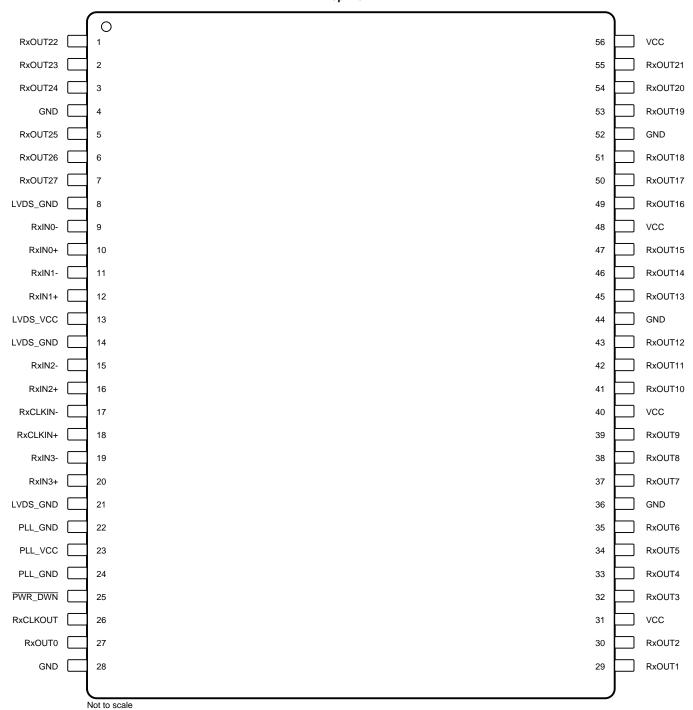
5 Pin Configuration and Functions

DGG Package 48-Pin TSSOP Top View





DGG Package 56-Pin TSSOP Top View



1

Product Folder Links: DS90CF366 DS90CF386



NZC Package 64-Pin NFBGA **Top View** 5 8 1 2 3 6 Α RxOUT17 VCC RxOUT15 GND RxOUT12 RxOUT8 RxOUT7 RxOUT6 В GND NC RxOUT16 RxOUT11 VCC GND RxOUT5 RxOUT3 С RxOUT21 NC RxOUT18 RxOUT14 RxOUT9 RxOUT4 NC RxOUT1 D VCC RxOUT20 RxOUT19 RxOUT13 RxOUT10 VCC RxOUT2 GND LVDS_ VCC Е RxOUT22 RxOUT24 GND LVDS_GND PWR_DWN RxCLKOUT RxOUT0 F RxOUT23 RxOUT26 NC RxIN1-RxIN2+ PLL_GND NC LVDS_GND RxOUT25 NC RxIN1+ RxIN2-RxIN3-LVDS_GND PLL_GND G LVDS_ RxOUT27 LVDS_GND RxCLKIN+ Н RxIN0-RxIN0+ RxCLKIN-RxIN3+ Not to scale

Pin Functions

	i iii i diletiona							
	PIN							
NAME	DS90CF366	DS900	F386	TYPE ⁽¹⁾	DESCRIPTION			
NAIVIE	TSSOP TSSOP NFBGA							
GND	3, 25, 32, 38, 44	4, 28, 36, 44, 52	A4, B1, B6, D8, E3	G	Ground pins for LVCMOS outputs.			
LVDS GND	7, 13, 18	8, 14, 21	E5, G3, G7, H5	G	Ground pins for LVDS inputs.			
LVDS V _{CC}	12	13	E4, H4	Р	Power supply pin for LVDS inputs.			
NC	6	_	B2, C2, C7, F3, F8, G2	_	Pins not connected.			
PLL GND	19, 21	22, 24	F6, G8	G	Ground pin for PLL.			
PLL V _{CC}	20	23	F7	Р	Power supply for PLL.			

(1) G = Ground, I = Input, O = Output, and P = Power



Pin Functions (continued)

Name		PIN							
NAME TSSOP TSSOP NFBGA		1		`E386	TVDE(1)	DESCRIPTION			
PWR DWN	NAME				1112	DESCINII TION			
RXCLKIN+ 17 18 H7 I Positive LVDS differential clock input. RXCLKIN- 16 17 H6 I Negative LVDS differential clock input. RXCLKOUT 23 26 E7 O LVCMOS level clock output. The falling edge acts as data strobe. RXINO+ 9 10 H33 I Positive LVDS differential data inputs. RXINO- 8 9 H2 I Negative LVDS differential data inputs. RXIN1- 10 11 F4 I Negative LVDS differential data inputs. RXIN1- 10 11 F4 I Negative LVDS differential data inputs. RXIN1- 15 16 F5 I Positive LVDS differential data inputs. RXIN1- 15 16 F5 I Positive LVDS differential data inputs. RXIN1- 19 66 I Negative LVDS differential data inputs. RXIN3- — 19 66 I Negative LVDS differential data inputs. RXIN3- — 19<	PWR DWN				ı	LVCMOS level input. When asserted (low input) the receiver			
RXCLKIN- 16 17 H6 I Negative LVDS differential clock input. RXCLKOUT 23 26 E7 O LVCMOS level clock output. The falling edge acts as data strobe. RXIND- 8 9 H2 I Negative LVDS differential data inputs. RXIN1- 11 12 G4 I Positive LVDS differential data inputs. RXIN1- 10 11 F4 I Negative LVDS differential data inputs. RXIN1- 15 16 F5 I Positive LVDS differential data inputs. RXIN12- 14 15 G5 I Negative LVDS differential data inputs. RXIN13- - 19 G6 I Negative LVDS differential data inputs. RXIN13- - 19 G6 I Negative LVDS differential data inputs. RXIN13- - 19 G6 I Negative LVDS differential data inputs. RXOUT1 26 29 C8 O LVCMOS level data output. RXOUT2 27	RxCLKIN+	17	18	H7	ı	-			
RXCLKOUT 23 26 E7 O LVCMOS level clock output. The falling edge acts as data strobe. RxIN0+ 9 10 H3 I Positive LVDS differential data inputs. RxIN0- 8 9 H2 I Negative LVDS differential data inputs. RxIN1+ 11 12 G4 I Positive LVDS differential data inputs. RxIN1- 10 111 F4 I Negative LVDS differential data inputs. RxIN1- 15 16 F5 I Positive LVDS differential data inputs. RxIN1- 14 15 G5 I Negative LVDS differential data inputs. RxIN13- - 20 H8 I Positive LVDS differential data inputs. RxIN13- - 19 G6 I Negative LVDS differential data inputs. RxIN13- - 19 G6 I Negative LVDS differential data inputs. RxIN13- - 19 G6 I Negative LVDS differential data inputs. RxOUT1 26 <td></td> <td>16</td> <td></td> <td>H6</td> <td>I</td> <td>·</td>		16		H6	I	·			
RxIN0- RxIN1- 11	RxCLKOUT	23	26	E7	0	LVCMOS level clock output. The falling edge acts as data			
RxIN1+ 11 12 G4 I Positive LVDS differential data inputs. RxIN1- 10 11 F4 I Negative LVDS differential data inputs. RxIN2+ 15 16 F5 I Positive LVDS differential data inputs. RxIN2- 14 15 G5 I Negative LVDS differential data inputs. RxIN3- — 19 G6 I Negative LVDS differential data inputs. RxIN3- — 19 G6 I Negative LVDS differential data inputs. RxOUT0 24 27 E8 O LVCMOS level data output. RxOUT1 26 29 C8 O LVCMOS level data output. RxOUT3 29 32 B8 O LVCMOS level data output. RxOUT3 29 32 B8 O LVCMOS level data output. RxOUT6 31 34 B7 O LVCMOS level data output. RxOUT6 33 35 A8 O LVCMOS level data outpu	RxIN0+	9	10	НЗ	I	Positive LVDS differential data inputs.			
RxIN1-	RxIN0-	8	9	H2	I	Negative LVDS differential data inputs.			
RxIN2+ 15 16 F5 I Positive LVDS differential data inputs. RxIN2- 14 15 G5 I Negative LVDS differential data inputs. RxIN3+ — 20 H8 I Positive LVDS differential data inputs. RxINI3- — 19 G6 I Negative LVDS differential data inputs. RxOUT0 24 27 E8 O LVCMOS level data output. RxOUT1 26 29 C8 O LVCMOS level data output. RxOUT3 29 32 B8 O LVCMOS level data output. RxOUT3 29 32 B8 O LVCMOS level data output. RxOUT3 30 33 C6 O LVCMOS level data output. RxOUT6 31 34 B7 O LVCMOS level data output. RxOUT7 34 37 A7 O LVCMOS level data output. RxOUT9 37 39 C5 O LVCMOS level data output.	RxIN1+	11	12	G4	I	Positive LVDS differential data inputs.			
RxiN2-	RxIN1-	10	11	F4	I	Negative LVDS differential data inputs.			
RxiN3+	RxIN2+	15	16	F5	I	Positive LVDS differential data inputs.			
Rxin3	RxIN2-	14	15	G5	I	Negative LVDS differential data inputs.			
RXOUTO 24 27 E8 O LVCMOS level data output.	RxIN3+	_	20	H8	I	Positive LVDS differential data inputs.			
RXOUT1 26 29 C8 O LVCMOS level data output. RXOUT2 27 30 D7 O LVCMOS level data output. RXOUT3 29 32 B8 O LVCMOS level data output. RXOUT4 30 33 C6 O LVCMOS level data output. RXOUT5 31 34 B7 O LVCMOS level data output. RXOUT6 33 35 A8 O LVCMOS level data output. RXOUT7 34 37 A7 O LVCMOS level data output. RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45	RxIN3-	_	19	G6	I	Negative LVDS differential data inputs.			
RXOUT2 27 30 D7 O LVCMOS level data output. RXOUT3 29 32 B8 O LVCMOS level data output. RXOUT4 30 33 C6 O LVCMOS level data output. RXOUT5 31 34 B7 O LVCMOS level data output. RXOUT6 33 35 A8 O LVCMOS level data output. RXOUT7 34 37 A7 O LVCMOS level data output. RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45	RxOUT0	24	27	E8	0	LVCMOS level data output.			
RXOUT3 29 32 B8 O LVCMOS level data output. RXOUT4 30 33 C6 O LVCMOS level data output. RXOUT5 31 34 B7 O LVCMOS level data output. RXOUT6 33 35 A8 O LVCMOS level data output. RXOUT7 34 37 A7 O LVCMOS level data output. RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46	RxOUT1	26	29	C8	0	LVCMOS level data output.			
RXOUT4 30 33 C6 O LVCMOS level data output. RXOUT5 31 34 B7 O LVCMOS level data output. RXOUT6 33 35 A8 O LVCMOS level data output. RXOUT7 34 37 A7 O LVCMOS level data output. RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1	RxOUT2	27	30	D7	0	LVCMOS level data output.			
RXOUTS 31 34 B7 O LVCMOS level data output. RXOUT6 33 35 A8 O LVCMOS level data output. RXOUT7 34 37 A7 O LVCMOS level data output. RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1	RxOUT3	29	32	B8	0	LVCMOS level data output.			
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RXOUT7 34 37 A7 O LVCMOS level data output. RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT29 5	RxOUT5	31	34	В7	0	LVCMOS level data output.			
RXOUT7 34 37 A7 O LVCMOS level data output. RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT20 5	RxOUT6	33	35	A8	0	LVCMOS level data output.			
RXOUT8 35 38 A6 O LVCMOS level data output. RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT29 4 53 D3 O LVCMOS level data output. RXOUT21 -						·			
RXOUT9 37 39 C5 O LVCMOS level data output. RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT23 —	RxOUT8	35	38	A6	0	·			
RXOUT10 39 41 D5 O LVCMOS level data output. RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT19 4 53 D3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT23 —	RxOUT9	37	39	C5	0	·			
RXOUT11 40 42 B4 O LVCMOS level data output. RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT19 4 53 D3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT23 — 2 F1 O LVCMOS level data output. RXOUT24 —	RxOUT10	39	41	D5	0	·			
RXOUT12 41 43 A5 O LVCMOS level data output. RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT19 4 53 D3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT23 — 1 E1 O LVCMOS level data output. RXOUT24 — 3 E2 O LVCMOS level data output. RXOUT25 —	RxOUT11	40	42	B4		·			
RXOUT13 43 45 D4 O LVCMOS level data output. RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT19 4 53 D3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT22 — 1 E1 O LVCMOS level data output. RXOUT23 — 2 F1 O LVCMOS level data output. RXOUT24 — 3 E2 O LVCMOS level data output. RXOUT25 — <t< td=""><td>RxOUT12</td><td>41</td><td>43</td><td>A5</td><td></td><td>·</td></t<>	RxOUT12	41	43	A5		·			
RXOUT14 45 46 C4 O LVCMOS level data output. RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT19 4 53 D3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT22 — 1 E1 O LVCMOS level data output. RXOUT23 — 2 F1 O LVCMOS level data output. RXOUT24 — 3 E2 O LVCMOS level data output. RXOUT25 — 5 G1 O LVCMOS level data output. RXOUT26 —	RxOUT13	43	45		0				
RXOUT15 46 47 A3 O LVCMOS level data output. RXOUT16 47 49 B3 O LVCMOS level data output. RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT19 4 53 D3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT22 — 1 E1 O LVCMOS level data output. RXOUT23 — 2 F1 O LVCMOS level data output. RXOUT24 — 3 E2 O LVCMOS level data output. RXOUT25 — 6 F2 O LVCMOS level data output. RXOUT27 — 7 H1 O LVCMOS level data output.									
RxOUT16 47 49 B3 O LVCMOS level data output. RxOUT17 1 50 A1 O LVCMOS level data output. RxOUT18 2 51 C3 O LVCMOS level data output. RxOUT19 4 53 D3 O LVCMOS level data output. RxOUT20 5 54 D2 O LVCMOS level data output. RxOUT21 — 55 C1 O LVCMOS level data output. RxOUT22 — 1 E1 O LVCMOS level data output. RxOUT23 — 2 F1 O LVCMOS level data output. RxOUT24 — 3 E2 O LVCMOS level data output. RxOUT25 — 5 G1 O LVCMOS level data output. RxOUT26 — 6 F2 O LVCMOS level data output. RxOUT27 — 7 H1 O LVCMOS level data output.						<u>'</u>			
RXOUT17 1 50 A1 O LVCMOS level data output. RXOUT18 2 51 C3 O LVCMOS level data output. RXOUT19 4 53 D3 O LVCMOS level data output. RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT22 — 1 E1 O LVCMOS level data output. RXOUT23 — 2 F1 O LVCMOS level data output. RXOUT24 — 3 E2 O LVCMOS level data output. RXOUT25 — 5 G1 O LVCMOS level data output. RXOUT26 — 6 F2 O LVCMOS level data output. RXOUT27 — 7 H1 O LVCMOS level data output.						'			
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RXOUT20 5 54 D2 O LVCMOS level data output. RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT22 — 1 E1 O LVCMOS level data output. RXOUT23 — 2 F1 O LVCMOS level data output. RXOUT24 — 3 E2 O LVCMOS level data output. RXOUT25 — 5 G1 O LVCMOS level data output. RXOUT26 — 6 F2 O LVCMOS level data output. RXOUT27 — 7 H1 O LVCMOS level data output.						·			
RXOUT21 — 55 C1 O LVCMOS level data output. RXOUT22 — 1 E1 O LVCMOS level data output. RXOUT23 — 2 F1 O LVCMOS level data output. RXOUT24 — 3 E2 O LVCMOS level data output. RXOUT25 — 5 G1 O LVCMOS level data output. RXOUT26 — 6 F2 O LVCMOS level data output. RXOUT27 — 7 H1 O LVCMOS level data output.						·			
RxOUT22 — 1 E1 O LVCMOS level data output. RxOUT23 — 2 F1 O LVCMOS level data output. RxOUT24 — 3 E2 O LVCMOS level data output. RxOUT25 — 5 G1 O LVCMOS level data output. RxOUT26 — 6 F2 O LVCMOS level data output. RXOUT27 — 7 H1 O LVCMOS level data output.		_				·			
RxOUT23 — 2 F1 O LVCMOS level data output. RxOUT24 — 3 E2 O LVCMOS level data output. RxOUT25 — 5 G1 O LVCMOS level data output. RxOUT26 — 6 F2 O LVCMOS level data output. RxOUT27 — 7 H1 O LVCMOS level data output.		_				·			
RxOUT24 — 3 E2 O LVCMOS level data output. RxOUT25 — 5 G1 O LVCMOS level data output. RxOUT26 — 6 F2 O LVCMOS level data output. RxOUT27 — 7 H1 O LVCMOS level data output.						-			
RxOUT25 — 5 G1 O LVCMOS level data output. RxOUT26 — 6 F2 O LVCMOS level data output. RxOUT27 — 7 H1 O LVCMOS level data output.									
RxOUT26 — 6 F2 O LVCMOS level data output. RxOUT27 — 7 H1 O LVCMOS level data output.		_							
RxOUT27 — 7 H1 O LVCMOS level data output.		_				·			
		_				·			
Voc. 28 36 42 48 31 40 48 56 A2 B5 D1 D6 P Power supply pins for LVCMOS outputs	V _{CC}	28, 36, 42, 48	31, 40, 48, 56	A2, B5, D1, D6	P	Power supply pins for LVCMOS outputs.			

Product Folder Links: DS90CF366 DS90CF386

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
Supply voltage, V _{CC}			-0.3	4	V
CMOS/LVCMOS output voltage				V _{CC} + 0.3	V
LVDS receiver input voltage			-0.3	V _{CC} + 0.3	V
	DS90CF366, TSSOP pa		1.61		
Power dissipation capacity at 25°C	50005000	TSSOP package		1.89	W
CMOS/LVCMOS output voltage LVDS receiver input voltage Power dissipation capacity at 25°C DS90C Lead temperature Operating junction temperature, TJ	DS90CF386	S90CF386 NFBGA package		2	
l and to men a matrice	TSSOP soldering (4 s)	OP soldering (4 s)		260	00
_ead temperature	NFBGA soldering, reflov	FBGA soldering, reflow (20 s)		220	°C
Operating junction temperature, T _J				150	°C
Storage temperature, T _{stg}			-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
\/	Floatroatotic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾		V
V _(ESD) Electrostatic discharge		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾		V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	3	3.3	3.6	V
	Receiver input	0		2.4	V
V _{NOISE}	Supply noise voltage			100	mV_PP
T _A	Operating free-air temperature	-10	25	70	°C

6.4 Thermal Information

		DS90CF366	DS900	CF386	
	THERMAL METRIC ⁽¹⁾		DGG (TSSOP)	NZC (NFBGA)	UNIT
		48 PINS	56 PINS	64 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	67.8	64.6	65.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	22.1	20.6	23.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	34.8	33.3	44.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.1	1	1	°C/W
ψ_{JB}	Junction-to-board characterization parameter	34.5	33	44.9	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

Product Folder Links: DS90CF366 DS90CF386

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIO	NS	MIN	TYP ⁽¹⁾	MAX	UNIT
LVCMOS	DC SPECIFICATIONS						
V _{IH}	High level input voltage			2		V_{CC}	V
V _{IL}	Low level input voltage			GND		0.8	V
V _{OH}	High level output voltage	$I_{OH} = -0.4 \text{ mA}$		2.7	3.3		V
V _{OL}	Low level output voltage	I _{OL} = 2 mA			0.06	0.3	V
V _{CL}	Input clamp voltage	I _{CL} = -18 mA			-0.79	-1.5	V
	land to compare	$V_{IN} = 0.4 \text{ V}, 2.5 \text{ V or } V_{CC}$			1.8	15	uA
I _{IN}	Input current	V _{IN} = GND		-10	0		uA
Ios	Output short circuit current	V _{OUT} = 0 V			-60	-120	mA
LVDS RE	ECEIVER DC SPECIFICATIONS						
V_{TH}	Differential input high threshold	V _{CM} = 1.2 V				100	mV
V _{TL}	Differential input low threshold			-100			mV
	land to compare	V _{IN} = 2.4 V, V _{CC} = 3.6 V				±10	μΑ
I _{IN}	Input current	V _{IN} = 0 V, V _{CC} = 3.6 V				±10	μΑ
RECEIVE	ER SUPPLY CURRENT						
		C _L = 8 pF, worst case pattern,	f = 32.5 MHz		49	70	mA
			f = 37.5 MHz		53	75	mA
		DS90CF386, see Figure 1 and Figure 4	f = 65 MHz		81	V _{CC} 0.8 3.3 .06 0.3 .79 -1.5 1.8 15 0 -60 -120 100 ±10 ±10 49 70 53 75 81 114 96 135 49 60 53 65 78 100 90 115 28 45 30 47 43 60 43 70	mA
ICCRW	Receiver supply current		f = 85 MHz		96	135	mA
ICCRVV	worst case		f = 32.5 MHz		49	60	mA
		C _L = 8 pF, worst case pattern,	f = 37.5 MHz		53	65	mA
		DS90CF366, see Figure 1 and Figure 4	f = 65 MHz		78	100	mA
			f = 85 MHz		90	115	mA
			f = 32.5 MHz		28	45	mA
ICCRG	Receiver supply current,	C _L = 8 pF, 16 grayscale pattern,	f = 37.5 MHz		30	47	mA
	16 grayscale	see Figure 2, Figure 3, and Figure 4 f = 65 MHz f = 85 MHz	f = 65 MHz		43	60	mA
			f = 85 MHz		43	70	mA
ICCRZ	Receiver supply current power down ⁽²⁾	Power Down = low receiver output power down mode	ts stay low during		140	400	μΑ

 ⁽¹⁾ Typical values are given for V_{CC} = 3.3 V and T_A = 25°C.
 (2) Current into device pins is defined as positive. Current out of device pins is defined as negative. Voltages are referenced to ground unless otherwise specified (except V_{OD} and ΔV _{OD}).



6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
CLHT	CMOS or LVCMOS low-to-high transition time	See Figure 4		2	3.5	ns
CHLT	CMOS or LVCMOS high-to-low transition time	See Figure 4		1.8	3.5	ns
RSPos0	Receiver input strobe position for bit 0	f = 85 MHz, see Figure 11 and Figure 12	0.49	0.84	1.19	ns
RSPos1	Receiver input strobe position for bit 1	f = 85 MHz	2.17	2.52	2.87	ns
RSPos2	Receiver input strobe position for bit 2	f = 85 MHz	3.85	4.2	4.55	ns
RSPos3	Receiver input strobe position for bit 3	f = 85 MHz	5.53	5.88	6.23	ns
RSPos4	Receiver input strobe position for bit 4	f = 85 MHz	7.21	7.56	7.91	ns
RSPos5	Receiver input strobe position for bit 5	f = 85 MHz	8.89	9.24	9.59	ns
RSPos6	Receiver input strobe position for bit 6	f = 85 MHz	10.57	10.92	11.27	ns
RSKM	RxIN skew margin (2)	f = 85 MHz, see Figure 13	290			ps
RCOP	RxCLK OUT period	See Figure 5	11.76	Т	50	ns
RCOH	RxCLK OUT high time	f = 85 MHz, see Figure 5	4.5	5	7	ns
RCOL	RxCLK OUT low time	f = 85 MHz, see Figure 5	4	5	6.5	ns
RSRC	RxOUT setup to RxCLK OUT	f = 85 MHz, see Figure 5	2			ns
RHRC	RxOUT hold to RxCLK OUT	f = 85 MHz, see Figure 5	3.5			ns
RCCD	RxCLK IN to RxCLK OUT delay	25°C, V _{CC} = 3.3 V, see Figure 6	5.5	7	9.5	ns
RPLLS	Receiver phase lock loop set	See Figure 7			10	ms
RPDD	Receiver power down delay	See Figure 10			1	μs

6.7 Timing Diagrams

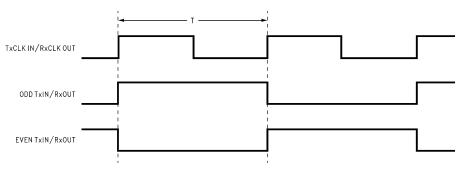
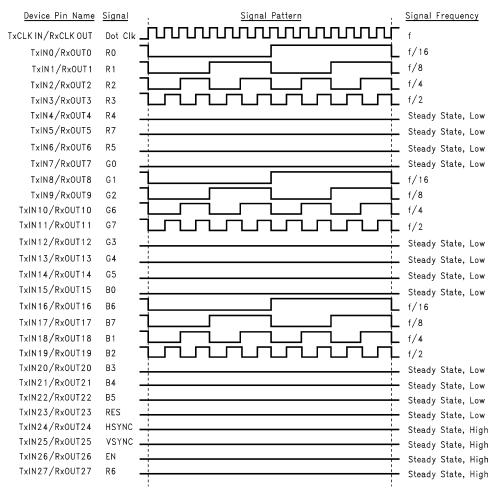


Figure 1. Test Pattern, Worst Case

Typical values are given for V_{CC} = 3.3 V and T_A = 25°C. Receiver skew margin is defined as the valid data sampling region at the receiver inputs. This margin takes into account the transmitter pulse positions (min and max) and the receiver input setup and hold time (internal data sampling window - RSPos). This margin allows for LVDS interconnect skew, inter-symbol interference (both dependent on type/length of cable), and clock jitter (less than 150 ps).

TEXAS INSTRUMENTS

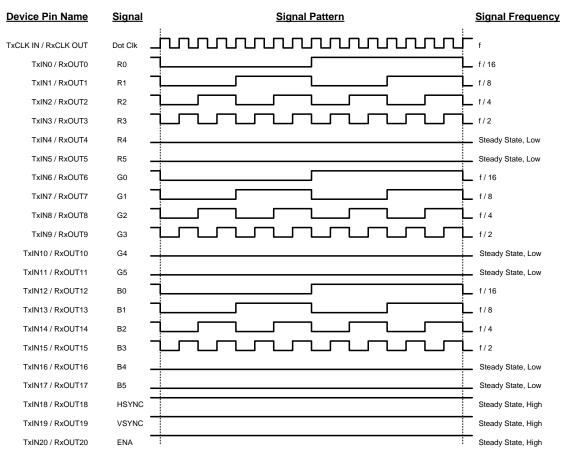
Timing Diagrams (continued)



- (1) The worst case test pattern produces a maximum toggling of digital circuits, LVDS I/O, and CMOS or LVCMOS I/O.
- (2) The 16 grayscale test pattern tests device power consumption for a *typical* LCD display pattern. The test pattern approximates signal switching needed to produce groups of 16 vertical stripes across the display.
- (3) Figure 1 and Figure 3 show a falling edge data strobe (TxCLK IN/RxCLK OUT).
- (4) Recommended pin to signal mapping. Customer may choose to define differently.

Figure 2. Test Pattern, 16 Grayscale (DS90CF386)





- (1) The worst case test pattern produces a maximum toggling of digital circuits, LVDS I/O, and CMOS or LVCMOS I/O.
- (2) The 16 grayscale test pattern tests device power consumption for a *typical* LCD display pattern. The test pattern approximates signal switching needed to produce groups of 16 vertical stripes across the display.
- (3) Figure 1 and Figure 3 show a falling edge data strobe (TxCLK IN/RxCLK OUT).
- (4) Recommended pin to signal mapping. Customer may choose to define differently.

Figure 3. Test Pattern, 16 Grayscale (DS90CF366)

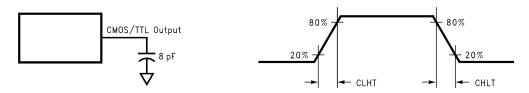


Figure 4. DS90CF3x6 (Receiver) CMOS or LVCMOS Output Load and Transition Times

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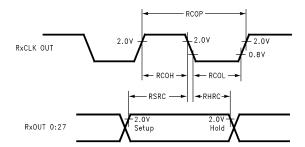


Figure 5. DS90CF3x6 (Receiver) Setup or Hold and High or Low Times

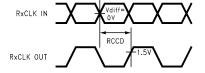


Figure 6. DS90CF3x6 (Receiver) Clock In to Clock Out Delay

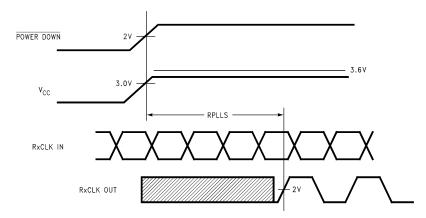


Figure 7. DS90CF3x6 (Receiver) Phase Lock Loop Set Time

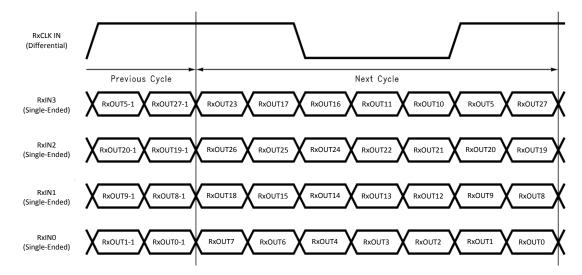


Figure 8. DS90CF386 Mapping of 28 LVCMOS Parallel Data to 4D + C LVDS Serialzied Data



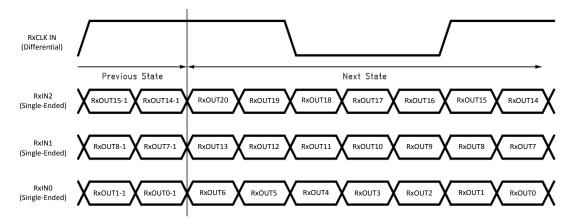


Figure 9. DS90CF366 Mapping of 21 LVCMOS Parallel Data to 3D + C LVDS Serialized Data

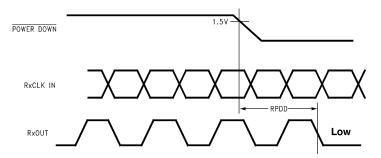


Figure 10. DS90CF3x6 (Receiver) Power Down Delay

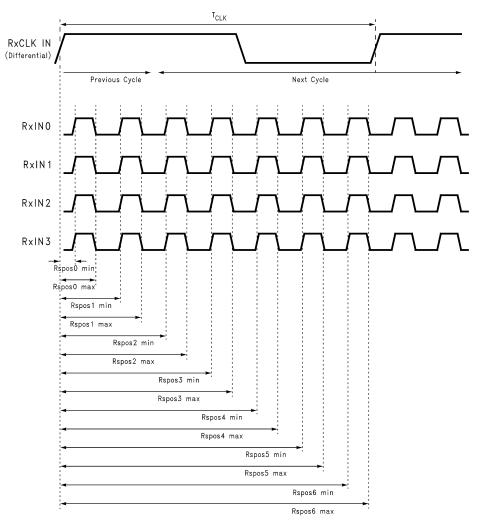


Figure 11. DS90CF386 (Receiver) LVDS Input Strobe Position



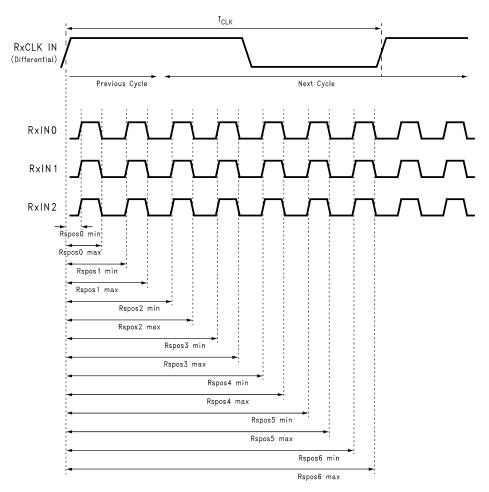
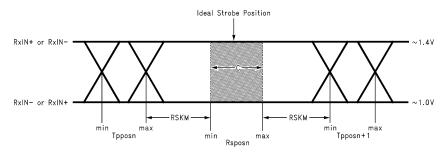


Figure 12. DS90CF366 (Receiver) LVDS Input Strobe Position



C: Setup and Hold Time (Internal data sampling window) defined by Rspos (receiver input strobe position) min and max

Tppos: Transmitter output pulse position (min and max)

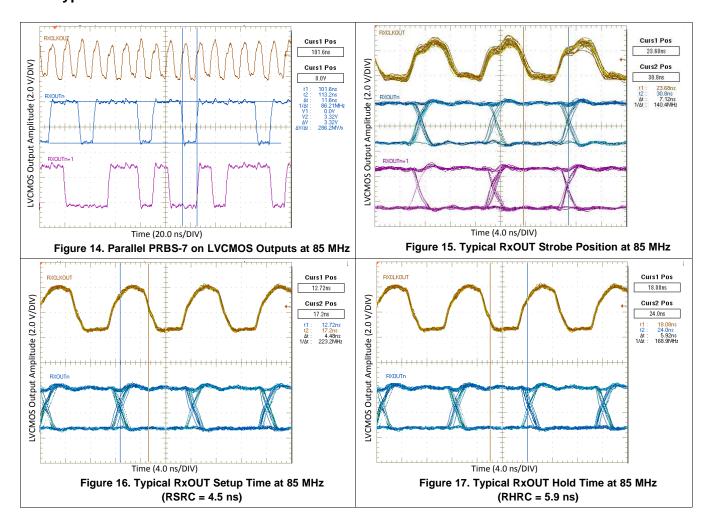
Cable skew: Typically 10 ps-40 ps per foot, media dependent

RSKM = Cable skew (type, length) + source clock jitter (cycle-to-cycle)⁽¹⁾ + ISI (inter-symbol interference)⁽²⁾

- (1) Cycle-to-cycle jitter depends on the Tx source. Clock jitter should be maintained to less than 250 ps at 85 MHz.
- (2) ISI is dependent on interconnect length; may be zero.

Figure 13. Receiver LVDS Input Skew Margin

6.8 Typical Characteristics





7 Detailed Description

7.1 Overview

The DS90CF386 is a receiver that converts four LVDS (Low Voltage Differential Signaling) data streams into parallel 28 bits of LVCMOS data (24 bits of RGB and 4 bits of HSYNC, VSYNC, DE, and CNTL). The DS90CF366 is a receiver that converts three LVDS data streams into parallel 21 bits of LVCMOS data (18 bits of RGB and 3 bits of HSYNC, VSYNC, and DE). An internal PLL locks to the incoming LVDS clock ranging from 20 to 85 MHz. The locked PLL ensures a stable clock to sample the output LVCMOS data on the Receiver Clock Out falling edge. These devices feature a PWR DWN pin to put the device into low power mode when there is no active input data.

7.2 Functional Block Diagrams

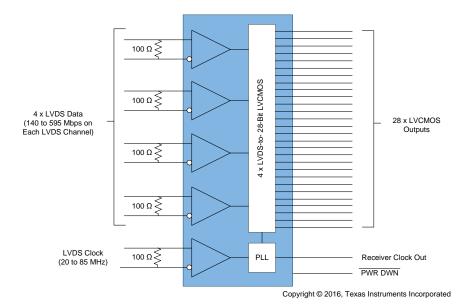


Figure 18. DS90CF386 Block Diagram

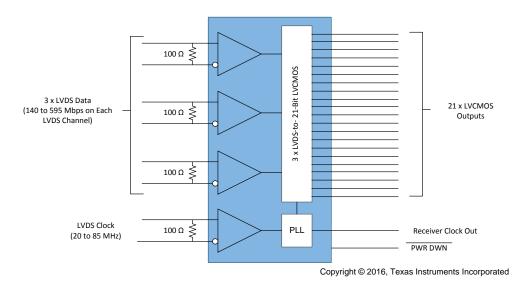


Figure 19. DS90CF366 Block Diagram

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7.3 Feature Description

The DS90CF386 and DS90CF366 consist of several key blocks:

- LVDS Receivers
- Phase Locked Loop (PLL)
- Serial LVDS-to-Parallel LVCMOS Converter
- LVCMOS Drivers

7.3.1 LVDS Receivers

There are five differential LVDS inputs to the DS90CF386 and four differential LVDS inputs to the DS90CF366. For the DS90CF386, four of the LVDS inputs contain serialized data originating from a 28-bit source transmitter. For the DS90CF366, three of the LVDS inputs contain serialized data originating from a 21-bit source transmitter. The remaining LVDS input contains the LVDS clock associated with the data pairs.

7.3.1.1 LVDS Input Termination

The DS90CF386 and DS90CF366 require a single $100-\Omega$ terminating resistor across the true and complement lines on each differential pair of the receiver input. To prevent reflections due to stubs, this resistor should be placed as close to the device input pins as possible. Figure 20 shows an example.

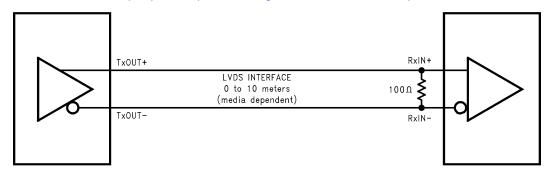


Figure 20. LVDS Serialized Link Termination

7.3.2 Phase Locked Loop (PLL)

The FPD Link I devices use an internal PLL to recover the clock transmitted across the LVDS interface. The recovered clock is then used as a reference to determine the sampling position of the seven serial bits received per clock cycle. The width of each bit in the serialized LVDS data stream is one-seventh the clock period. Differential skew (Δt within one differential pair), interconnect skew (Δt of one differential pair to another), and clock jitter will all reduce the available window for sampling the LVDS serial data streams. Individual bypassing of each V_{CC} to ground will minimize the noise passed on to the PLL, thus creating a low jitter LVDS clock to improve the overall jitter budget.

7.3.3 Serial LVDS-to-Parallel LVCMOS Converter

After the PLL locks to the incoming LVDS clock, the receiver deserializes each LVDS differential data pair into seven parallel LVCMOS data outputs per clock cycle. For the DS90CF386, the LVDS data inputs map to LVCMOS outputs according to Figure 8. For the DS90CF366, the LVDS data inputs map to LVCMOS outputs according to Figure 9.

7.3.4 LVCMOS Drivers

The LVCMOS outputs from the DS90CF386 and DS90CF366 are the deserialized parallel single-ended data from the serialized LVDS differential data pairs. Each LVCMOS output is clocked by the PLL and strobes on the RxCLKOUT falling edge. All unused DS90CF386 and DS90CF366 RxOUT outputs can be left floating.

Product Folder Links: DS90CF366 DS90CF386



7.4 Device Functional Modes

7.4.1 Power Sequencing and Power-Down Mode

The DS90CF386 and DS90CF366 may be placed into a power down mode at any time by asserting the PWR DWN pin (active low). The DS90CF386 and DS90CF366 are also designed to protect themselves from accidental loss of power to either the transmitter or receiver. If power to the transmit board is lost, the receiver clocks (input and output) stop. The data outputs (RxOUT) retain the states they were in when the clocks stopped. When the receiver board loses power, the receiver inputs are controlled by a failsafe bias circuitry. The LVDS inputs are High-Z during initial power on and power off conditions. Current is limited to 5 mA per input, thus avoiding the potential for latch-up when powering the device.

Product Folder Links: DS90CF366 DS90CF386



8 Application and Implementation

NOTE

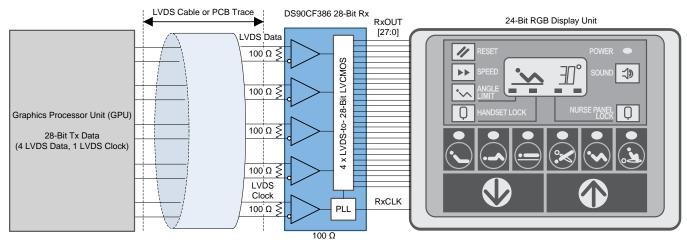
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The DS90F386 and DS90CF366 are designed for a wide variety of data transmission applications. The use of serialized LVDS data lines in these applications allows for efficient signal transmission over a narrow bus width, thereby reducing cost, power, and space.

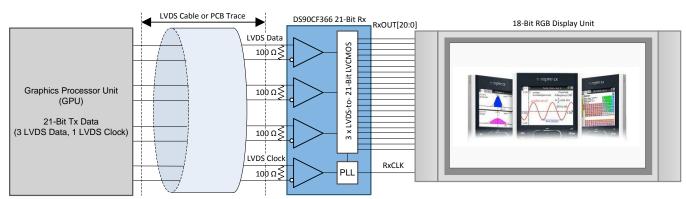
8.2 Typical Applications

Figure 21 and Figure 22 show typical applications of the DS90CF386 and DS90CF366 for displays when used as an OpenLDI-to-RGB bridge.



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Figure 21. Typical DS90CF386 Application Block Diagram



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Figure 22. Typical DS90CF366 Application Block Diagram

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Typical Applications (continued)

8.2.1 Design Requirements

For this design example, follow the requirements in Table 1.

Table 1. Design Parameters

PARAMETER	DESIGN REQUIREMENTS
Operating frequency	LVDS clock must be within 20 MHz to 85 MHz.
Bit resolution	DS90CF386: No higher than 24 bpp. The maximum supported resolution is 8-bit RGB. DS90CF366: No higher than 18 bpp. The maximum supported resolution is 6-bit RGB.
Bit data mapping	Determine the appropriate mapping required by the panel display following the DS90CF386 or DS90CF366 outputs.
RSKM (Receiver skew margin)	Ensure that there is acceptable margin between Tx pulse position and Rx strobe position.
Input termination for RxIN±	Inputs require a 100 Ω ± 10% resistor across each LVDS differential pair. Place as close as possible to IC input pins.
RxIN± board trace impedance	Design differential trace impedance with 100 Ω ±5%
LVCMOS outputs	If unused, leave pins floating. Series resistance on each LVCMOS output optional to reduce reflections from long board traces. If used, $33-\Omega$ series resistance is typical.
DC power supply coupling capacitors	Use a 0.1- μ F capacitor to minimize power supply noise. Place as close as possible to V_{CC} pins.

8.2.2 Detailed Design Procedure

To design with the DS90CF386 or DS90CF366, determine the following:

- Cable Interface
- Bit Resolution and Operating Frequency
- Bit Mapping from Receiver to Endpoint Panel Display
- RSKM Interoperability with Transmitter Pulse Position Margin

8.2.2.1 Cables

A cable interface between the transmitter and receiver needs to support the differential LVDS pairs. The DS90CF366 requires four pairs of signal wires and the DS90CF386 requires five pairs of signal wires. The ideal cable interface has a constant 100-Ω differential impedance throughout the path. It is also recommended that cable skew remain below 120 ps (assuming 85 MHz clock rate) to maintain a sufficient data sampling window at the receiver.

Depending upon the application and data rate, the interconnecting media between Tx and Rx may vary. For example, for lower data rate (clock rate) and shorter cable lengths (< 2m), the media electrical performance is less critical. For higher speed or long distance applications, the media's performance becomes more critical. Certain cable constructions provide tighter skew (matched electrical length between the conductors and pairs). For example, twin-coax cables have been demonstrated at distances as long as five meters and with the maximum data transfer of 2.38 Gbps (DS90CF366) and 1.785 Gbps (DS90CF386).

8.2.2.2 Bit Resolution and Operating Frequency Compatibility

The bit resolution of the endpoint panel display reveals whether there are enough bits available in the DS90CF386 or DS90CF366 to output the required data per pixel. The DS90CF386 has 28 parallel LVCMOS outputs and can therefore provide a bit resolution up to 24 bpp (bits per pixel). In each clock cycle, the remaining bits are the three control signals (HSync, VSync, DE) and one spare bit. The DS90CF366 has 21 parallel LVCMOS outputs and can therefore provide a bit resolution up to 18 bpp (bits per pixel). In each clock cycle, the remaining bits are the three control signals (HSync, VSync, DE).

The number of pixels per frame and the refresh rate of the endpoint panel display indicate the required operating frequency of the descrializer clock. To determine the required clock frequency, refer to Equation 1.

Product Folder Links: DS90CF366 DS90CF386

f_Clk = [H_Active + H_Blank] x [V_Active + V_Blank] x f_Vertical

where

H_Active = Active Display Horizontal Lines

(1)



- H_Blank = Blanking Period Horizontal Lines
- V_Active = Active Display Vertical Lines
- V_Blank = Blanking Period Vertical Lines
- f Vertical = Refresh Rate (in Hz)
- f_Clk = Operating Frequency of LVDS clock

In each frame, there is a blanking period associated with horizontal rows and vertical columns that are not actively displayed on the panel. These blanking period pixels must be included to determine the required clock frequency. Consider the following example to determine the required LVDS clock frequency:

- H Active = 640
- H Blank = 40
- V_Active = 480
- V Blank = 41
- f_Vertical = 59.95 Hz

Thus, the required operating frequency is determined with Equation 2.

$$[640 + 40] \times [480 + 41] \times 59.95 = 21239086 \text{ Hz} \approx 21.24 \text{ MHz}$$
 (2)

Since the operating frequency for the PLL in the DS90CF386 and DS90CF366 ranges from 20 to 85 MHz, the DS90CF386 and DS90CF366 can support a panel display with the aforementioned requirements.

If the specific blanking interval is unknown, the number of pixels in the blanking interval can be approximated to 20% of the active pixels. Equation 3 can be used as a conservative approximation for the operating LVDS clock frequency:

$$f_Clk \approx H_Active \times V_Active \times f_Vertical \times 1.2$$
 (3)

Using this approximation, the operating frequency for the example in this section is estimated with Equation 4.

$$640 \times 480 \times 59.95 \times 1.2 = 22099968 \text{ Hz} \approx 22.10 \text{ MHz}$$
 (4)

8.2.2.3 Data Mapping between Receiver and Endpoint Panel Display

Ensure that the LVCMOS outputs are mapped to align with the endpoint display RGB mapping requirements following the deserializer. See the following for two popular mapping topologies for 8-bit RGB data.

- 1. LSBs are mapped to RxIN3±.
- 2. MSBs are mapped to RxIN3±.

Table 2 and Table 3 depict how these two popular topologies can be mapped to the DS90CF386 outputs.

Table 2. 8-Bit Color Mapping with LSBs on RxIN3±

LVDS INPUT CHANNEL	LVDS BIT STREAM POSITION	LVCMOS OUTPUT CHANNEL	COLOR MAPPING	COMMENTS
	TxIN0	RxOUT0	R2	
	TxIN1	RxOUT1	R3	
DalNo	TxIN2	RxOUT2	R4	
RxIN0	TxIN3	RxOUT3	R5	
	TxIN4	RxOUT4	R6	
	TxIN6	RxOUT6	R7	MSB
	TxIN7	RxOUT7	G2	
	TxIN8	RxOUT8	G3	
	TxIN9	RxOUT9	G4	
DuINA	TxIN12	RxOUT12	G5	
RxIN1	TxIN13	RxOUT13	G6	
	TxIN14	RxOUT14	G7	MSB
	TxIN15	RxOUT15	B2	
	TxIN18	RxOUT18	B3	

Product Folder Links: DS90CF366 DS90CF386



Table 2. 8-Bit Color Mapping with LSBs on RxIN3± (continued)

LVDS INPUT CHANNEL	LVDS BIT STREAM POSITION	LVCMOS OUTPUT CHANNEL	COLOR MAPPING	COMMENTS
	TxIN19	RxOUT19	B4	
	TxIN20	RxOUT20	B5	
	TxIN21	RxOUT21	B6	
RxIN2	TxIN22	RxOUT22	B7	MSB
	TxIN24	RxOUT24	HSYNC	Horizontal sync
	TxIN25	RxOUT25	VSYNC	Vertical sync
	TxIN26	RxOUT26	DE	Data enable
	TxIN27	RxOUT27	R0	LSB
	TxIN5	RxOUT5	R1	
	TxIN10	RxOUT10	G0	LSB
RxIN3	TxIN11	RxOUT11	G1	
	TxIN16	RxOUT16	В0	LSB
	TxIN17	RxOUT17	B1	
	TxIN23	RxOUT23	GP	General purpose

Table 3. 8-Bit Color Mapping with MSBs on RxIN3±

LVDS INPUT CHANNEL	LVDS BIT STREAM POSITION	LVCMOS OUTPUT CHANNEL	COLOR MAPPING	COMMENTS
	TxIN0	RxOUT0	R0	LSB
	TxIN1	RxOUT1	R1	
D.JNO	TxIN2	RxOUT2	R2	
RxIN0	TxIN3	RxOUT3	R3	
	TxIN4	RxOUT4	R4	
	TxIN6	RxOUT6	R5	
	TxIN7	RxOUT7	G0	LSB
	TxIN8	RxOUT8	G1	
	TxIN9	RxOUT9	G2	
RxIN1	TxIN12	RxOUT12	G3	
RXINT	TxIN13	RxOUT13	G4	
	TxIN14	RxOUT14	G5	
	TxIN15	RxOUT15	В0	LSB
	TxIN18	RxOUT18	B1	
	TxIN19	RxOUT19	B2	
	TxIN20	RxOUT20	B3	
	TxIN21	RxOUT21	B4	
RxIN2	TxIN22	RxOUT22	B5	
	TxIN24	RxOUT24	HSYNC	Horizontal sync
	TxIN25	RxOUT25	VSYNC	Vertical sync
	TxIN26	RxOUT26	DE	Data enable
	TxIN27	RxOUT27	R6	
	TxIN5	RxOUT5	R7	MSB
	TxIN10	RxOUT10	G6	
RxIN3	TxIN11	RxOUT11	G7	MSB
	TxIN16	RxOUT16	B6	
	TxIN17	RxOUT17	B7	MSB
	TxIN23	RxOUT23	GP	General purpose

Product Folder Links: DS90CF366 DS90CF386



In the case where either DS90CF386 or DS90CF366 is used to support 18 bpp, Table 2 is commonly used, where RxIN3± (if applicable) is left as *No Connect*. With this mapping, MSBs of RGB data are retained on RXIN0±, RXIN1±, and RXIN2± while the two LSBs for the original 8-bit RGB resolution are ignored from RxIN3±.

8.2.2.4 RSKM Interoperability

One of the most important factors when designing the receiver into a system application is assessing how much RSKM (Receiver Skew Margin) is available. In each LVDS clock cycle, the LVDS data stream carries seven serialized data bits. Ideally, the Transmit Pulse Position for each bit will occur every ($n \times T$)/7 seconds, where n = Bit Position and T = LVDS Clock Period. Likewise, ideally the Rx Strobe Position for each bit will occur every ($(n + 0.5) \times T$)/7 seconds. However, in real systems, both LVDS Tx and Rx will have non-ideal pulse and strobe position for each bit position due to the effects of cable skew, clock jitter, and ISI. This concept is illustrated in Figure 23.

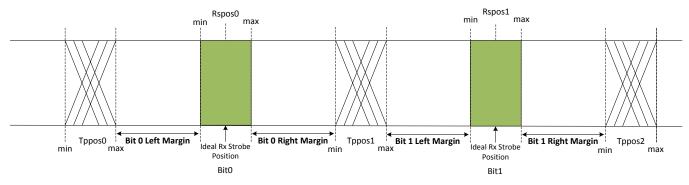


Figure 23. RSKM Measurement Example

All left and right margins for Bits 0-6 must be considered in order to determine the absolute minimum for the whole LVDS bit stream. This absolute minimum corresponds to the RSKM.

To improve RSKM performance between LVDS transmitter and receiver, designers often either advance or delay the LVDS clock compared to the LVDS data. Moving the LVDS clock compared to the LVDS data can improve the location of the setup and hold time for the transmitter compared to the setup and hold time for the receiver.

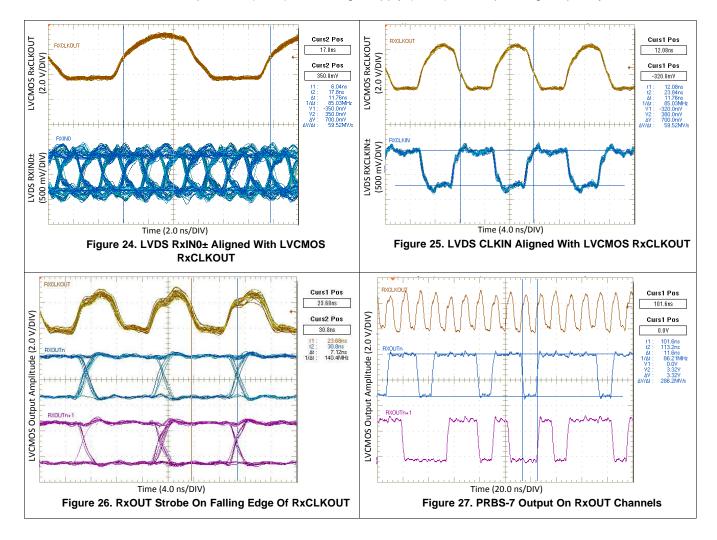
If there is less left bit margin than right bit margin, the LVDS clock can be delayed so that the Rx strobe position for incoming data appears to be delayed. If there is less right bit margin than left bit margin, all the LVDS data pairs can be delayed uniformly so that the LVDS clock and Rx strobe position for incoming data appear to advance. To delay an LVDS data or clock pair, designers either add more PCB trace length or install a capacitor between the LVDS transmitter and receiver. It is important to note that when using these techniques, all serialized bit positions are shifted right or left uniformly.

When designing the DS90CF386 or DS90CF366 receiver with a third-party OpenLDI transmitter, users must calculate the skew margin budget (RSKM) based on the Tx pulse position and the Rx strobe position to ensure error-free transmission. For more information about calculating RSKM, refer to Application Note, *Receiver Skew Margin for Channel Link I and FPD Link I Devices* (SNLA249).



8.2.3 Application Curves

The following application curves are examples taken with a DS90C385A serializer interfacing to a DS90CF386 deserializer with nominal temperature (25°C) and voltage supply (3.3 V) at an operating frequency of 85 MHz.





9 Power Supply Recommendations

Proper power supply decoupling is important to ensure a stable power supply with minimal power supply noise. Bypassing capacitors are needed to reduce the impact of switching noise which could limit performance. For a conservative approach, three parallel-connected decoupling capacitors (multi-layered ceramic type in surface mount form factor) between each V_{CC} (V_{CC} , PLL V_{CC} , LVDS V_{CC}) and the ground plane(s) are recommended. The three capacitor values are 0.1 μF , 0.01 μF , and 0.001 μF . The preferred capacitor size is 0402. An example is shown in Figure 28. The designer should employ wide traces for power and ground and ensure each capacitor has its own via to the ground plane. This helps to reduce overall inductance with regards to power supply filtering. If board space is limiting the number of bypass capacitors, the PLL V_{CC} should receive the most filtering. Next would be the LVDS V_{CC} pins and finally the logic V_{CC} pins.

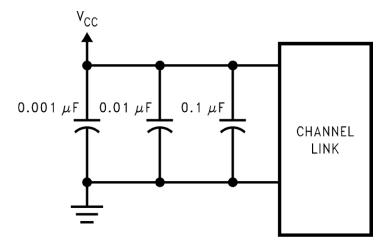


Figure 28. Recommended Bypass Capacitor Decoupling Configuration for V_{CC} , PLL V_{CC} , and LVDS V_{CC}

10 Layout

10.1 Layout Guidelines

As with any high speed design, board designers must maximize signal integrity by limiting reflections and crosstalk that can adversely affect high frequency and EMI performance. The following practices are recommended layout guidelines to optimize device performance.

- Ensure that differential pair traces are always closely coupled to eliminate noise interference from other signals and take full advantage of the common mode noise canceling effect of the differential signals.
- · Maintain equal length on signal traces for a given differential pair.
- · Limit impedance discontinuities by reducing the number of vias on signal traces.
- Eliminate any 90° angles on traces and use 45° bends instead.
- If a via must exist on one signal polarity, mirror the via implementation on the other polarity of the differential pair.
- Match the differential impedance of the selected physical media. This impedance should also match the value of the termination resistor that is connected across the differential pair at the receiver's input.
- When possible, use short traces for LVDS inputs.

10.2 Layout Examples

The following images show an example layout of the DS90CF386. Traces in blue correspond to the top layer and the traces in green correspond to the bottom layer. Note that differential pair inputs to the DS90CF386 are tightly coupled and close to the connector pins. In addition, observe that the power supply decoupling capacitors are placed as close as possible to the power supply pins with through vias in order to minimize inductance. The principles illustrated in this layout can also be applied to the 48-pin DS90CF366.

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Layout Examples (continued)

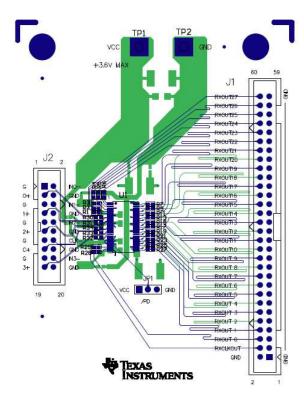


Figure 29. Example Layout With DS90CF386 (U1)

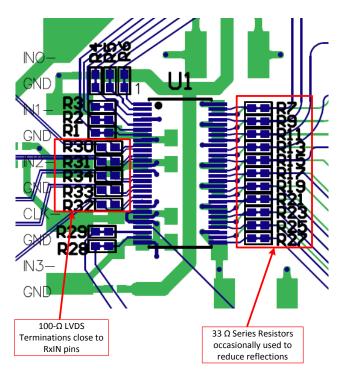


Figure 30. Example Layout Close-Up

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Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

Application Note, Receiver Skew Margin for Channel Link I and FPD Link I Devices, SNLA249

11.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.5 Glossary

SLYZ022 — TI Glossarv.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: DS90CF366 DS90CF386

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PACKAGING INFORMATION

								1	
Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	0
							(6)		
DS90CF366MTD/NOPB	ACTIVE	TSSOP	DGG	48	38	RoHS & Green	SN	Level-2-260C-1 YEAR	
DS90CF366MTDX/NOPB	ACTIVE	TSSOP	DGG	48	1000	RoHS & Green	SN	Level-2-260C-1 YEAR	
DS90CF386MTD	LIFEBUY	TSSOP	DGG	56	34	Non-RoHS & Green	Call TI	Level-2-235C-1 YEAR	
DS90CF386MTD/NOPB	ACTIVE	TSSOP	DGG	56	34	RoHS & Green	SN	Level-2-260C-1 YEAR	
DS90CF386MTDX/NOPB	ACTIVE	TSSOP	DGG	56	1000	RoHS & Green	SN	Level-2-260C-1 YEAR	
DS90CF386SLC/NOPB	ACTIVE	NFBGA	NZC	64	360	RoHS & Green	SNAGCU	Level-4-260C-72 HR	
DS90CF386SLCX/NOPB	ACTIVE	NFBGA	NZC	64	2000	RoHS & Green	SNAGCU	Level-4-260C-72 HR	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including to do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in spreference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000pp flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

Addendum-Page 1





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(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a lift of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/E lines if the finish value exceeds the maximum column width.

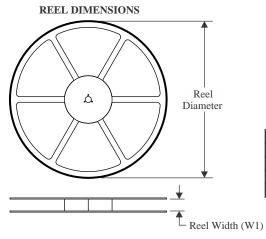
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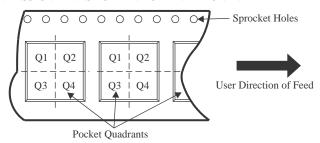
TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO PI BO Cavity A0

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

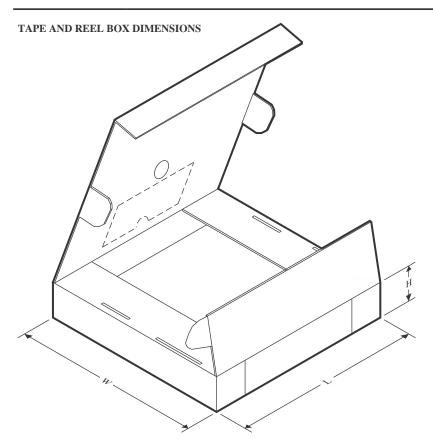


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS90CF366MTDX/NOPB	TSSOP	DGG	48	1000	330.0	24.4	8.6	13.2	1.6	12.0	24.0	Q1
DS90CF386MTDX/NOPB	TSSOP	DGG	56	1000	330.0	24.4	8.6	14.5	1.8	12.0	24.0	Q1
DS90CF386SLCX/NOPB	NFBGA	NZC	64	2000	330.0	16.4	8.3	8.3	2.3	12.0	16.0	Q1

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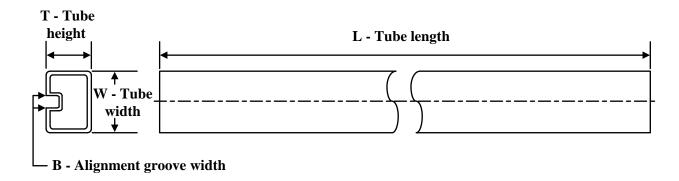
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS90CF366MTDX/NOPB	TSSOP	DGG	48	1000	367.0	367.0	45.0
DS90CF386MTDX/NOPB	TSSOP	DGG	56	1000	367.0	367.0	45.0
DS90CF386SLCX/NOPB	NFBGA	NZC	64	2000	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE



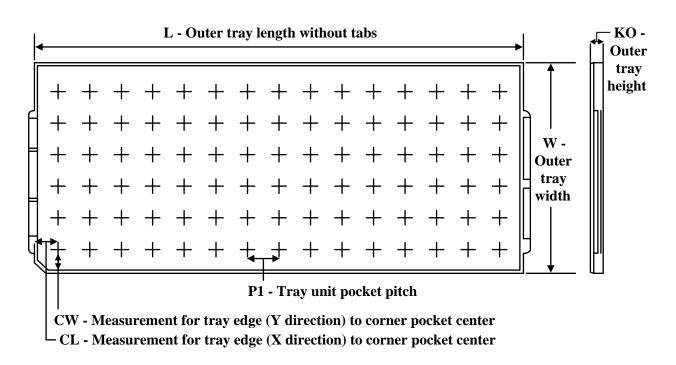
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
DS90CF366MTD/NOPB	DGG	TSSOP	48	38	495	10	2540	5.79
DS90CF386MTD	DGG	TSSOP	56	34	495	10	2540	5.79
DS90CF386MTD	DGG	TSSOP	56	34	495	10	2540	5.79
DS90CF386MTD/NOPB	DGG	TSSOP	56	34	495	10	2540	5.79



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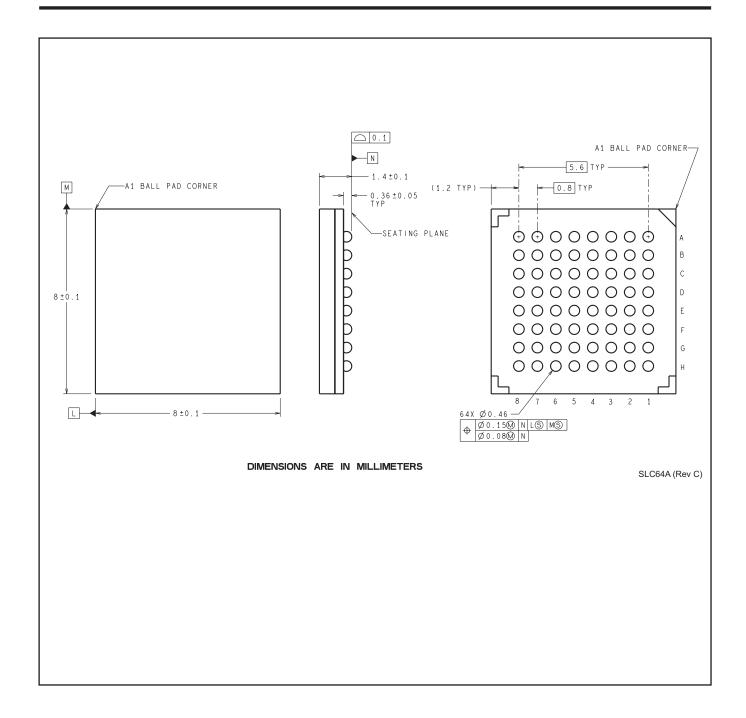
TRAY



Chamfer on Tray corner indicates Pin 1 orientation of packed units.

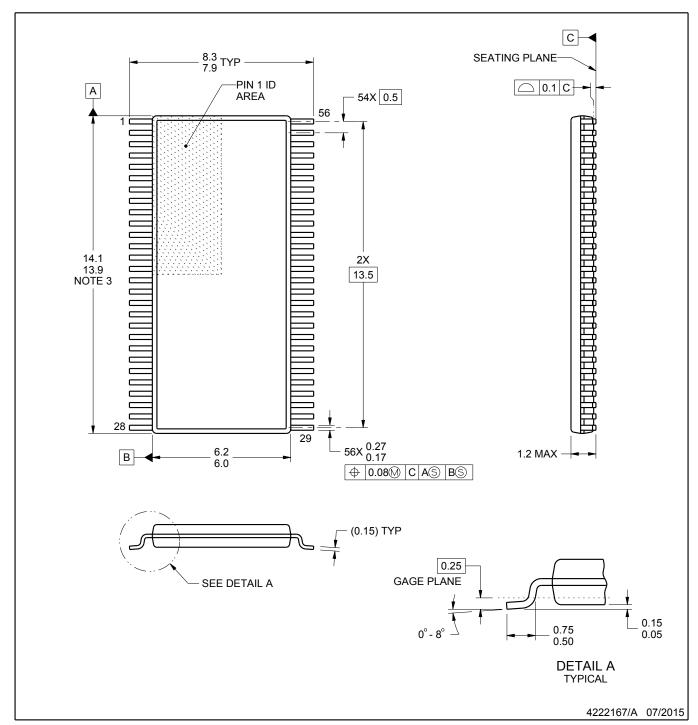
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	Unit array matrix	Max temperature (°C)	L (mm)	W (mm)	Κ0 (μm)	P1 (mm)	CL (mm)	CW (mm)
DS90CF386SLC/NOPB	NZC	NFBGA	64	360	12 x 30	150	322.6	135.9	7620	10	12.5	12.95







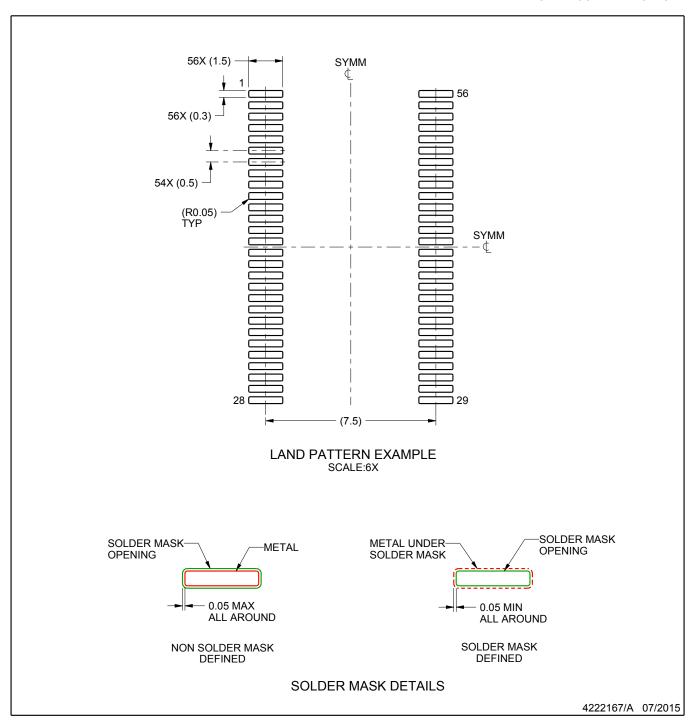


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

 4. Reference JEDEC registration MO-153.

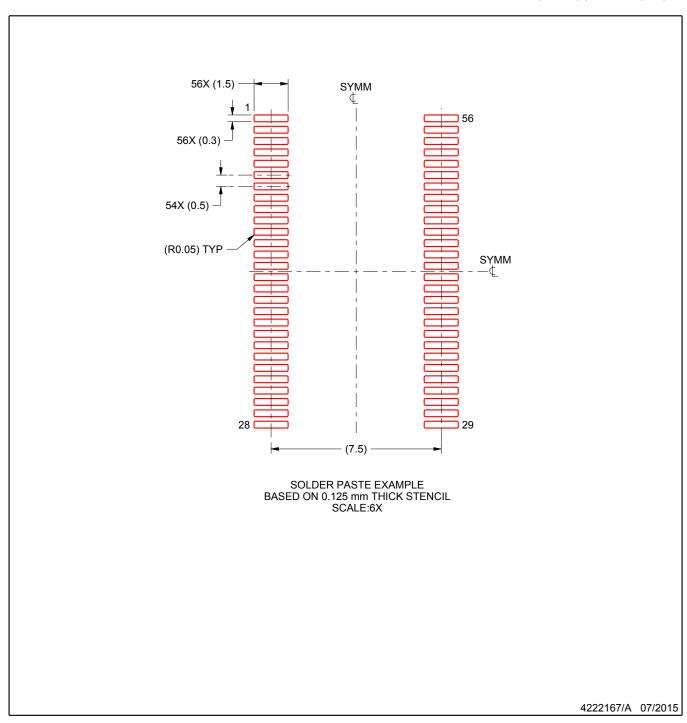




NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



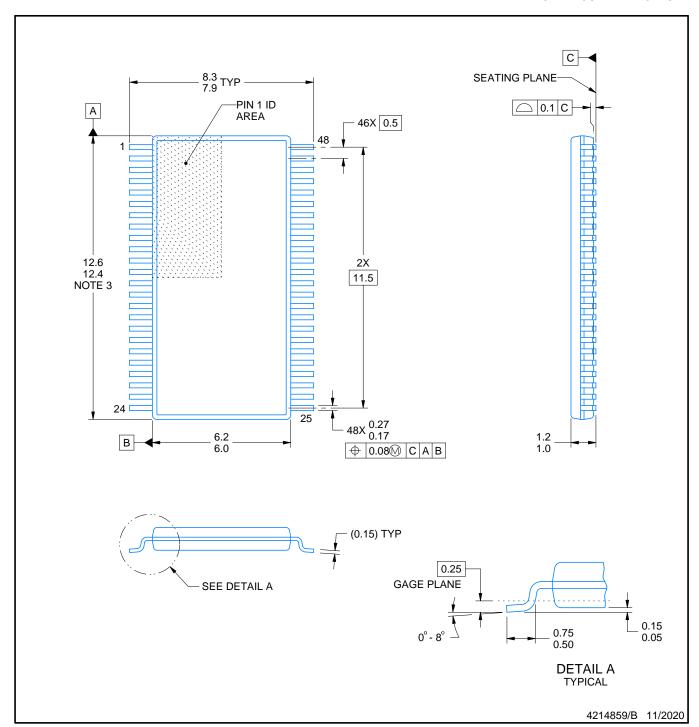


NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.8. Board assembly site may have different recommendations for stencil design.





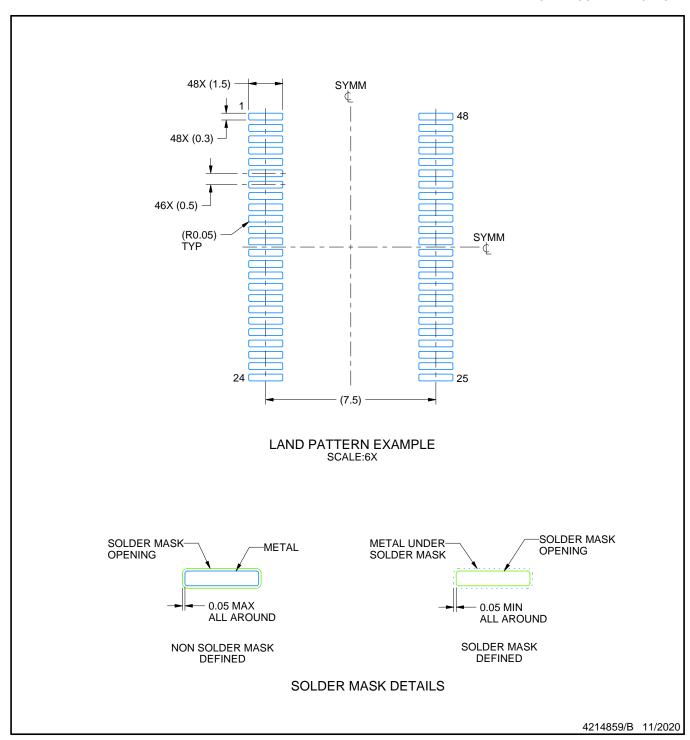


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
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- exceed 0.15 mm per side.

 4. Reference JEDEC registration MO-153.

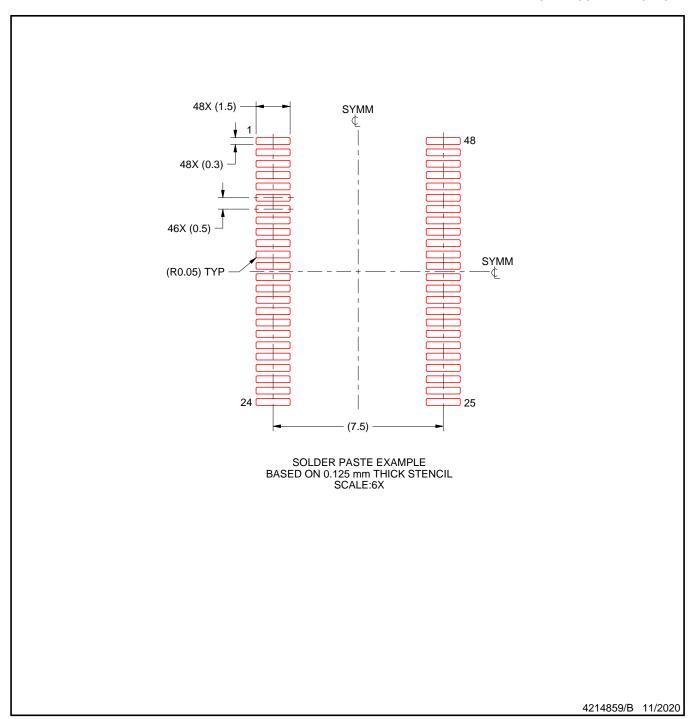




NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

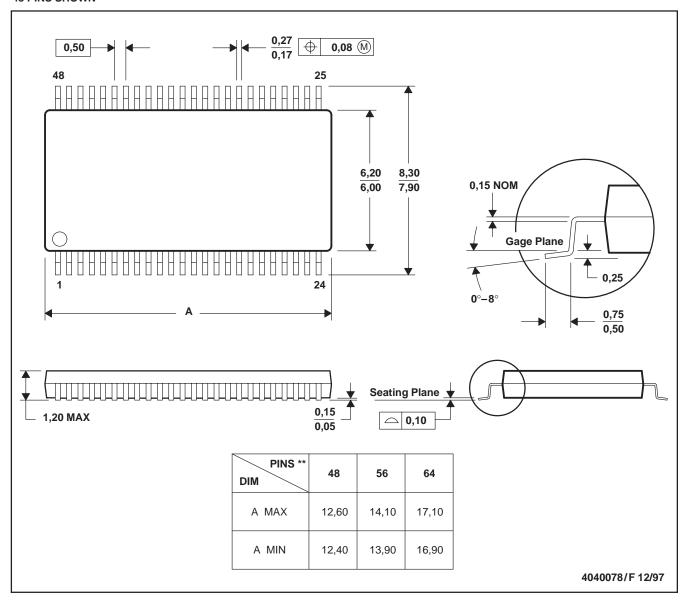
- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



DGG (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

48 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153

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